



SN74LVC2G08 Dual 2-Input Positive-AND Gate

1 Features

- Available in the Texas Instruments NanoStar™ and NanoFree™ Package
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Max t_{pd} of 4.7 ns at 3.3 V
- Low Power Consumption, 10- μ A Maximum I_{CC}
- ± 24 -mA Output Drive at 3.3 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at $V_{CC} = 3.3$ V, $T_A = 25^\circ\text{C}$
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at $V_{CC} = 3.3$ V, $T_A = 25^\circ\text{C}$
- I_{off} Supports Live Insertion, Partial-Power-Down Mode, and Back-Drive Protection
- Can Be Used as a Down Translator to Translate Inputs From a Maximum of 5.5 V Down to the V_{CC} Level
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human Body Model (A114-A)
 - 1000-V Charged-Device Model (C101)

2 Applications

- IP Phones: Wired and Wireless
- Optical Networking: EPON and Video Over Fiber
- Point-to-Point Microwave Backhaul
- Power: Telecom DC/DC Module: Analog
- Power: Telecom DC/DC Module: Digital
- Private Branch Exchange (PBX)
- Telecom Shelter: Power Distribution Unit (PDU)
- Vector Signal Analyzers and Generators
- Wireless Communications Testers
- Wireless Repeaters
- xDSL Modem/DSLAM

3 Description

This dual 2-input positive-AND gate is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC2G08 device performs the Boolean function $Y = A \times B$ or $Y = \overline{A + B}$ in positive logic.

NanoFree package technology is a major breakthrough in IC packaging concepts, using the die as the package.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
SN74LVC2G08DCT	SM8 (8)	2.95 mm × 2.80 mm
SN74LVC2G08DCU	VSSOP (8)	2.30 mm × 2.00 mm
SN74LVC2G08YZP	DSBGA (8)	1.91 mm × 0.91 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Logic Diagram (Positive Logic)

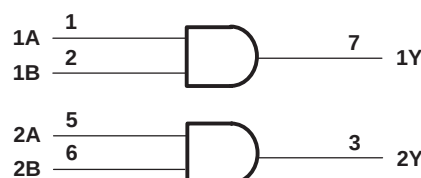


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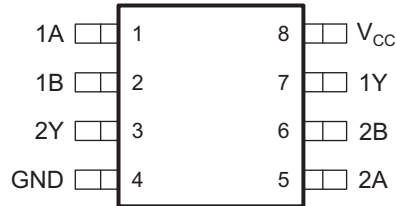
4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

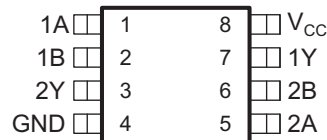
Changes from Revision M (April 2014) to Revision N	Page
Added <i>Pin Configuration and Functions</i> section, <i>ESD Ratings</i> and <i>Thermal Information</i> tables, <i>Feature Description</i> section, <i>Device Functional Modes</i> section, <i>Application and Implementation</i> section, <i>Power Supply Recommendations</i> section, <i>Layout</i> section, <i>Device and Documentation Support</i> section, and <i>Mechanical, Packaging, and Orderable Information</i> section	1

5 Pin Configuration and Functions

**DCT Package
8-Pin SM8
Top View**



**DCU Package
8-Pin VSSOP
Top View**



**YZP Package
8-Pin DSBGA
Bottom View**



Pin Functions⁽¹⁾

PIN		I/O	DESCRIPTION
NAME	NO.		
1A	1	I	Channel 1 logic input
1B	2	I	Channel 1 logic input
1Y	7	O	Logic level output
2A	5	I	Channel 2 logic input
2B	6	I	Channel 2 logic input
2Y	3	O	Logic level output
GND	4	—	Ground
V _{CC}	8	—	Power Supply

(1) See [Mechanical, Packaging, and Orderable Information](#) for dimensions.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage	−0.5	6.5	V
V _I	Input voltage ⁽²⁾	−0.5	6.5	V
V _O	Voltage applied to any output in the high-impedance or power-off state ⁽²⁾	−0.5	6.5	V
V _O	Voltage applied to any output in the high or low state ⁽²⁾⁽³⁾	−0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0		−50 mA
I _{OK}	Output clamp current	V _O < 0		−50 mA
I _O	Continuous output current			±50 mA
	Continuous current through V _{CC} or GND			±100 mA
T _j	Junction temperature			150 °C
T _{stg}	Storage temperature	−65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) The value of V_{CC} is provided in the *Recommended Operating Conditions* table.

6.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions⁽¹⁾

		MIN	MAX	UNIT	
V _{CC}	Supply voltage	Operating	1.65	5.5	V
		Data retention only	1.5		
V _{IH}	High-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}		V
		V _{CC} = 2.3 V to 2.7 V	1.7		
		V _{CC} = 3 V to 3.6 V	2		
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}		
V _{IL}	Low-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.35 × V _{CC}		V
		V _{CC} = 2.3 V to 2.7 V	0.7		
		V _{CC} = 3 V to 3.6 V	0.8		
		V _{CC} = 4.5 V to 5.5 V	0.3 × V _{CC}		
V _I	Input voltage	0	5.5	V	
V _O	Output voltage	0	V _{CC}	V	
I _{OH}	High-level output current	V _{CC} = 1.65 V	–4		mA
		V _{CC} = 2.3 V	–8		
		V _{CC} = 3 V	–16		
			–24		
	V _{CC} = 4.5 V	–32			
I _{OL}	Low-level output current	V _{CC} = 1.65 V	4		mA
		V _{CC} = 2.3 V	8		
		V _{CC} = 3 V	16		
			24		
	V _{CC} = 4.5 V	32			
Δt/Δv	Input transition rise or fall rate	V _{CC} = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V	20		ns/V
		V _{CC} = 3.3 V ± 0.3 V	10		
		V _{CC} = 5 V ± 0.5 V	5		
T _A	Operating free-air temperature	SN74LVC2G08DCU	–40	125	°C
		SN74LVC2G08DCT	–40	125	
		SN74LVC2G08YZP	–40	85	

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number [SCBA004](#).

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74LVC2G08			UNIT
		DCT (SM8)	DCU (VSSOP)	YZP (DSBGA)	
		8 PINS	8 PINS	8 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	220	227	128	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	108	84	14	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

SN74LVC2G08

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6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

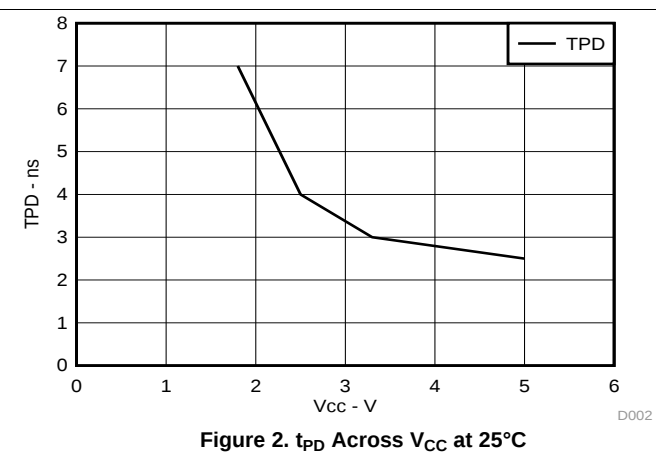
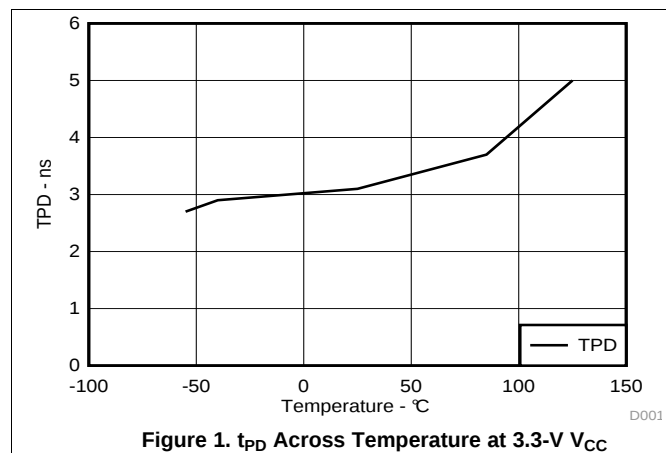
PARAMETER		TEST CONDITIONS	V _{CC}	MIN	TYP ⁽¹⁾	MAX	UNIT
V _{OH}		I _{OH} = –100 µA	1.65 V to 5.5 V	V _{CC} – 0.1			V
		I _{OH} = –4 mA	1.65 V	1.2			
		I _{OH} = –8 mA	2.3 V	1.9			
		I _{OH} = –16 mA	3 V	2.4			
		I _{OH} = –24 mA		2.3			
		I _{OH} = –32 mA	4.5 V	3.8			
V _{OL}		I _{OL} = 100 µA	1.65 V to 5.5 V	0.1			V
		I _{OL} = 4 mA	1.65 V	0.45			
		I _{OL} = 8 mA	2.3 V	0.3			
		I _{OL} = 16 mA	3 V	0.4			
		I _{OL} = 24 mA		0.55			
		I _{OL} = 32 mA	4.5 V	0.55			
I _I	A or B inputs	V _I = 5.5 V or GND	0 to 5.5 V	±5			µA
I _{off}		V _I or V _O = 5.5 V	0	±10			µA
I _{CC}		V _I = 5.5 V or GND, I _O = 0	1.65 V to 5.5 V	10			µA
ΔI _{CC}		One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND, T _A = –40°C to 85°C	3 V to 5.5 V	500			µA
C _i		V _I = V _{CC} or GND, T _A = –40°C to 85°C	3.3 V	5			pF
C _{pd}		f = 10 MHz, T _A = –40°C to 85°C	1.8 V to 3.3V	17			
			5 V	20			

(1) All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

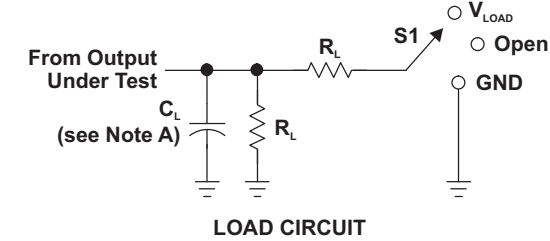
6.6 Switching Characteristics

PARAMETER	FROM (INPUT)	TO (OUTPUT)	T _A	V _{CC}	MIN	MAX	UNIT
t _{pd}	A or B	Y	–40°C to 85°C	V _{CC} = 1.8 V ± 0.15 V	2.6	9	ns
				V _{CC} = 2.5 V ± 0.2 V	1	5.1	
				V _{CC} = 3.3 V ± 0.3 V	1	4.7	
				V _{CC} = 5 V ± 0.5 V	1	3.8	
			–40°C to 125°C	V _{CC} = 1.8 V ± 0.15 V	2.6	9.8	
				V _{CC} = 2.5 V ± 0.2 V	1	5.8	
				V _{CC} = 3.3 V ± 0.3 V	1	5.3	
				V _{CC} = 5 V ± 0.5 V	1	4.8	

6.7 Typical Characteristics

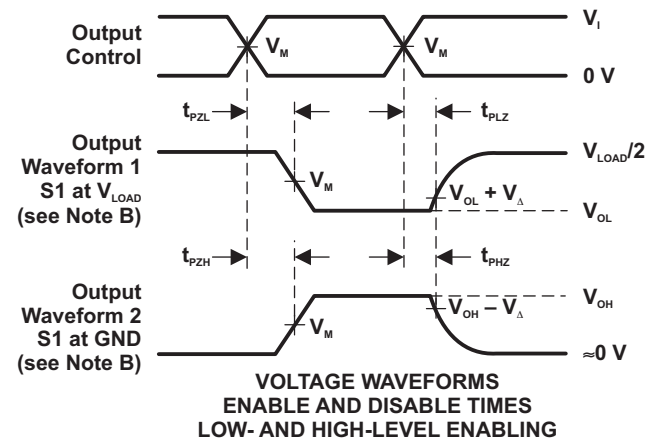
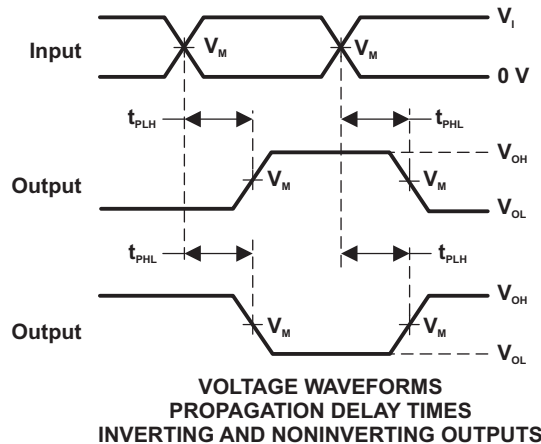
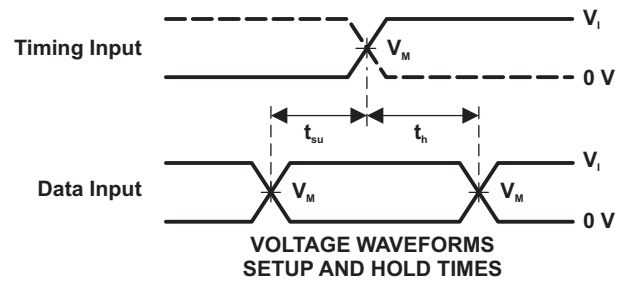
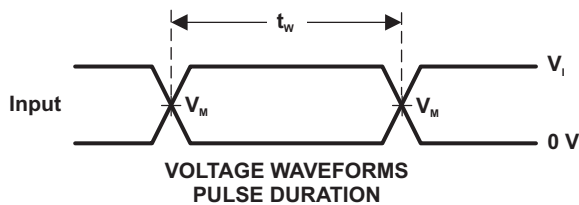


7 Parameter Measurement Information



TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_{Δ}
	V_I	t_i/t_f					
$1.8\text{ V} \pm 0.15\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	1 k Ω	0.15 V
$2.5\text{ V} \pm 0.2\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	500 Ω	0.15 V
$3.3\text{ V} \pm 0.3\text{ V}$	3 V	$\leq 2.5\text{ ns}$	1.5 V	6 V	50 pF	500 Ω	0.3 V
$5\text{ V} \pm 0.5\text{ V}$	V_{CC}	$\leq 2.5\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	50 pF	500 Ω	0.3 V



- NOTES:
- C_L includes probe and jig capacitance.
 - Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - All input pulses are supplied by generators having the following characteristics: PRR $\leq 10\text{ MHz}$, $Z_o = 50\ \Omega$.
 - The outputs are measured one at a time, with one transition per measurement.
 - t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - t_{PZL} and t_{PZH} are the same as t_{en} .
 - t_{PLH} and t_{PHL} are the same as t_{pd} .
 - All parameters and waveforms are not applicable to all devices.

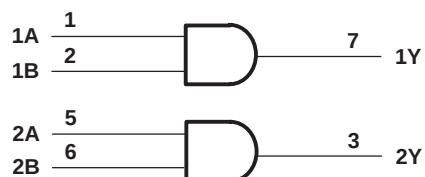
Figure 3. Load Circuit and Voltage Waveforms

8 Detailed Description

8.1 Overview

The SN74LVC1G06 device contains two positive-AND gates with a maximum sink current of 24 mA. A very low tpd of 4.7ns at 3.3V makes the device ideal for high speed applications. Additionally, 5.5V tolerant inputs allow the device to be used as a down translator if needed.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Down Voltage Translation

SN74LVC2G08 allows for logic input and output signals up to 5.5 V. While operating at V_{CC} of 3.3 V, the device will still recognize 5.5 V as a valid high input, however, the resulting output will be 3.3 V. This is the same for other voltage levels in the device effectively down translating any input logic level higher than V_{CC} but lower or equal to 5.5 V.

8.4 Device Functional Modes

[Table 1](#) lists the functional modes of the SN74LVC2G08.

Table 1. Function Table

INPUTS		OUTPUT Y
A	B	
H	H	H
L	X	L
X	L	L

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The SN74LVC2G08 is a high-drive CMOS device that can be used for implementing AND logic with a high output drive, such as an LED application. It can produce 24 mA of drive current at 3.3 V, making it ideal for driving multiple outputs and good for high-speed applications up to 100 MHz. The inputs are 5.5-V tolerant allowing it to translate down to V_{CC} .

9.2 Typical Application

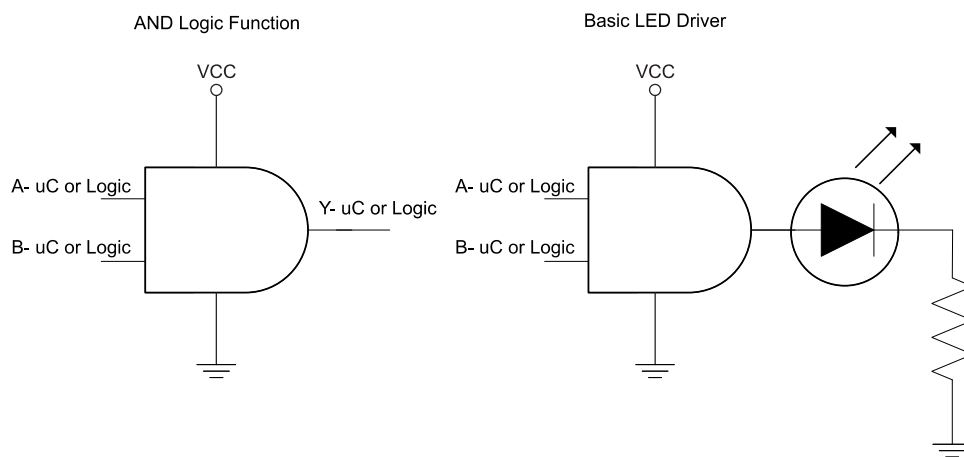


Figure 4. Typical Application

9.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads so routing and load conditions must be considered to prevent ringing.

9.2.2 Detailed Design Procedure

1. Recommended Input Conditions
 - Rise time and fall time specs. See ($\Delta t/\Delta V$) in the [Recommended Operating Conditions](#) table.
 - Specified high and low levels. See (V_{IH} and V_{IL}) in the [Recommended Operating Conditions](#) table.
 - Inputs are overvoltage tolerant allowing them to go as high as (V_I maximum) in the [Recommended Operating Conditions](#) table at any valid V_{CC} .
2. Recommended Output Conditions
 - Load currents must not exceed (I_O maximum) per output and must not exceed total current (continuous current through V_{CC} or GND) for the part. These limits are located in the [Recommended Operating Conditions](#) table.
 - Outputs must not be pulled above V_{CC} in normal operating conditions.

Typical Application (continued)

9.2.3 Application Curves

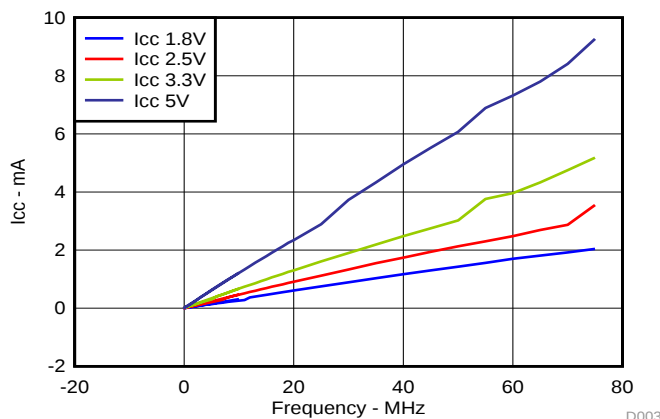


Figure 5. I_{CC} vs Frequency

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the [Recommended Operating Conditions](#) table. Each V_{CC} pin must have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1-μF capacitor is recommended and if there are multiple V_{CC} pins then 0.01-μF or 0.022-μF capacitor is recommended for each power pin. It is ok to parallel multiple bypass capacitors to reject different frequencies of noise. 0.1-μF and 1-μF capacitors are commonly used in parallel. The bypass capacitor must be installed as close to the power pin as possible for best results

11 Layout

11.1 Layout Guidelines

When using multiple bit logic devices inputs must not ever float. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. Specified below are the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V_{CC} whichever make more sense or is more convenient.

11.2 Layout Example

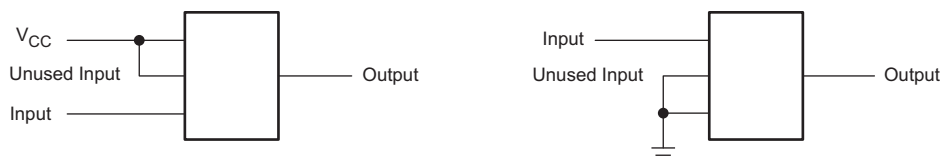


Figure 6. Layout Example

12 Device and Documentation Support

12.1 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.2 Trademarks

NanoStar, NanoFree, E2E are trademarks of Texas Instruments.
All other trademarks are the property of their respective owners.

12.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.4 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC2G08DCTR	ACTIVE	SM8	DCT	8	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C08 (R, Z)	Samples
SN74LVC2G08DCTRE4	ACTIVE	SM8	DCT	8	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C08 (R, Z)	Samples
SN74LVC2G08DCTRG4	ACTIVE	SM8	DCT	8	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C08 (R, Z)	Samples
SN74LVC2G08DCUR	ACTIVE	VSSOP	DCU	8	3000	Green (RoHS & no Sb/Br)	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(08, C08Q, C08R) (CR, CZ)	Samples
SN74LVC2G08DCURE4	ACTIVE	VSSOP	DCU	8	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C08R	Samples
SN74LVC2G08DCURG4	ACTIVE	VSSOP	DCU	8	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C08R	Samples
SN74LVC2G08DCUT	ACTIVE	VSSOP	DCU	8	250	Green (RoHS & no Sb/Br)	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(C08Q, C08R) CR	Samples
SN74LVC2G08DCUTG4	ACTIVE	VSSOP	DCU	8	250	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C08R	Samples
SN74LVC2G08YZPR	ACTIVE	DSBGA	YZP	8	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(CE7, CEN)	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN74LVC2G08 :

- Automotive: [SN74LVC2G08-Q1](#)
- Enhanced Product: [SN74LVC2G08-EP](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Enhanced Product - Supports Defense, Aerospace and Medical Applications

TAPE AND REEL INFORMATION


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC2G08DCTR	SM8	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
SN74LVC2G08DCUR	VSSOP	DCU	8	3000	180.0	9.0	2.05	3.3	1.0	4.0	8.0	Q3
SN74LVC2G08DCUR	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G08DCUR	VSSOP	DCU	8	3000	178.0	9.5	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G08DCURG4	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G08DCUT	VSSOP	DCU	8	250	178.0	9.5	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G08DCUT	VSSOP	DCU	8	250	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G08DCUTG4	VSSOP	DCU	8	250	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G08YZPR	DSBGA	YZP	8	3000	178.0	9.2	1.02	2.02	0.63	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS

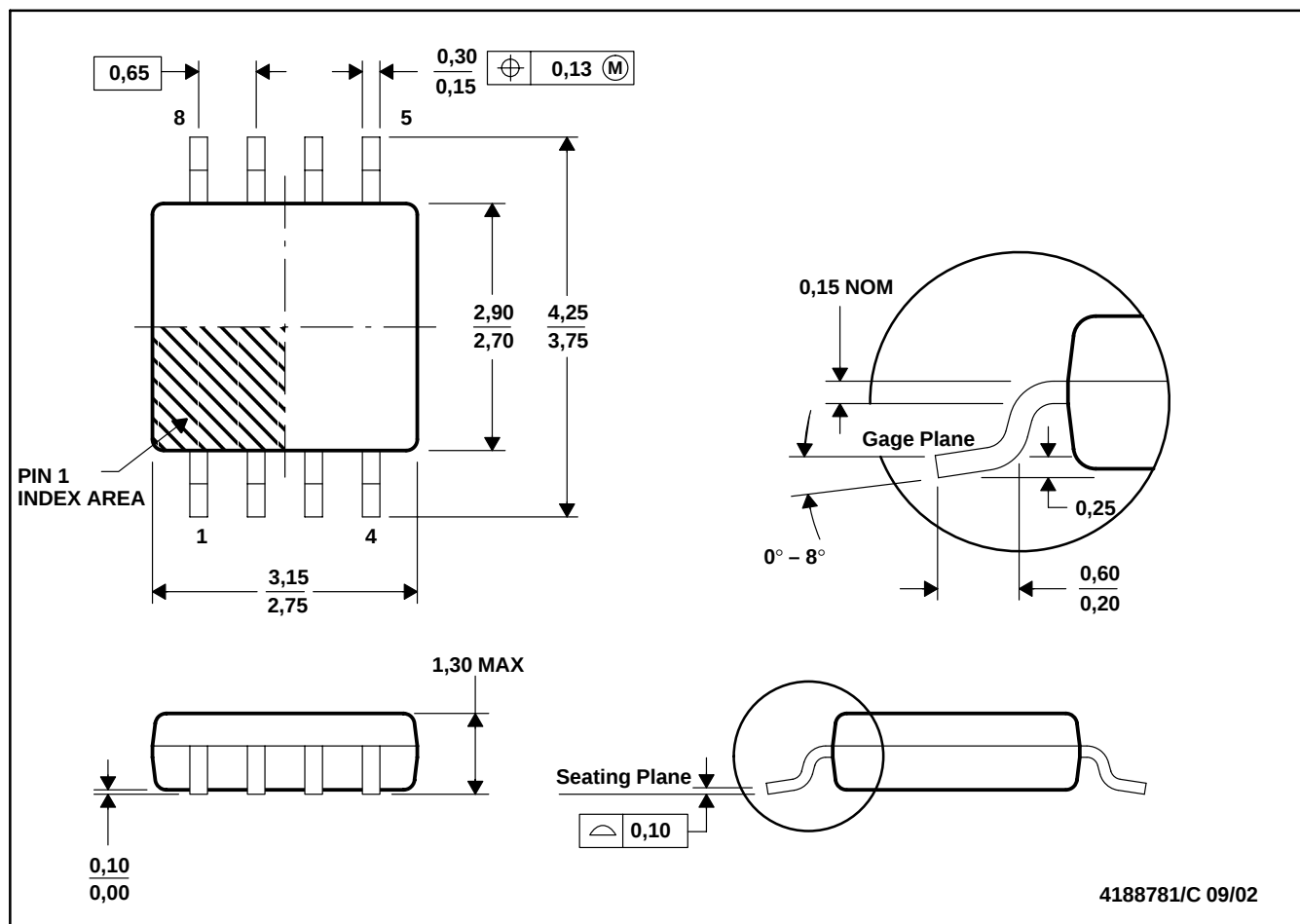


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC2G08DCTR	SM8	DCT	8	3000	182.0	182.0	20.0
SN74LVC2G08DCUR	VSSOP	DCU	8	3000	182.0	182.0	20.0
SN74LVC2G08DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74LVC2G08DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74LVC2G08DCURG4	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74LVC2G08DCUT	VSSOP	DCU	8	250	202.0	201.0	28.0
SN74LVC2G08DCUT	VSSOP	DCU	8	250	202.0	201.0	28.0
SN74LVC2G08DCUTG4	VSSOP	DCU	8	250	202.0	201.0	28.0
SN74LVC2G08YZPR	DSBGA	YZP	8	3000	220.0	220.0	35.0

DCT (R-PDSO-G8)

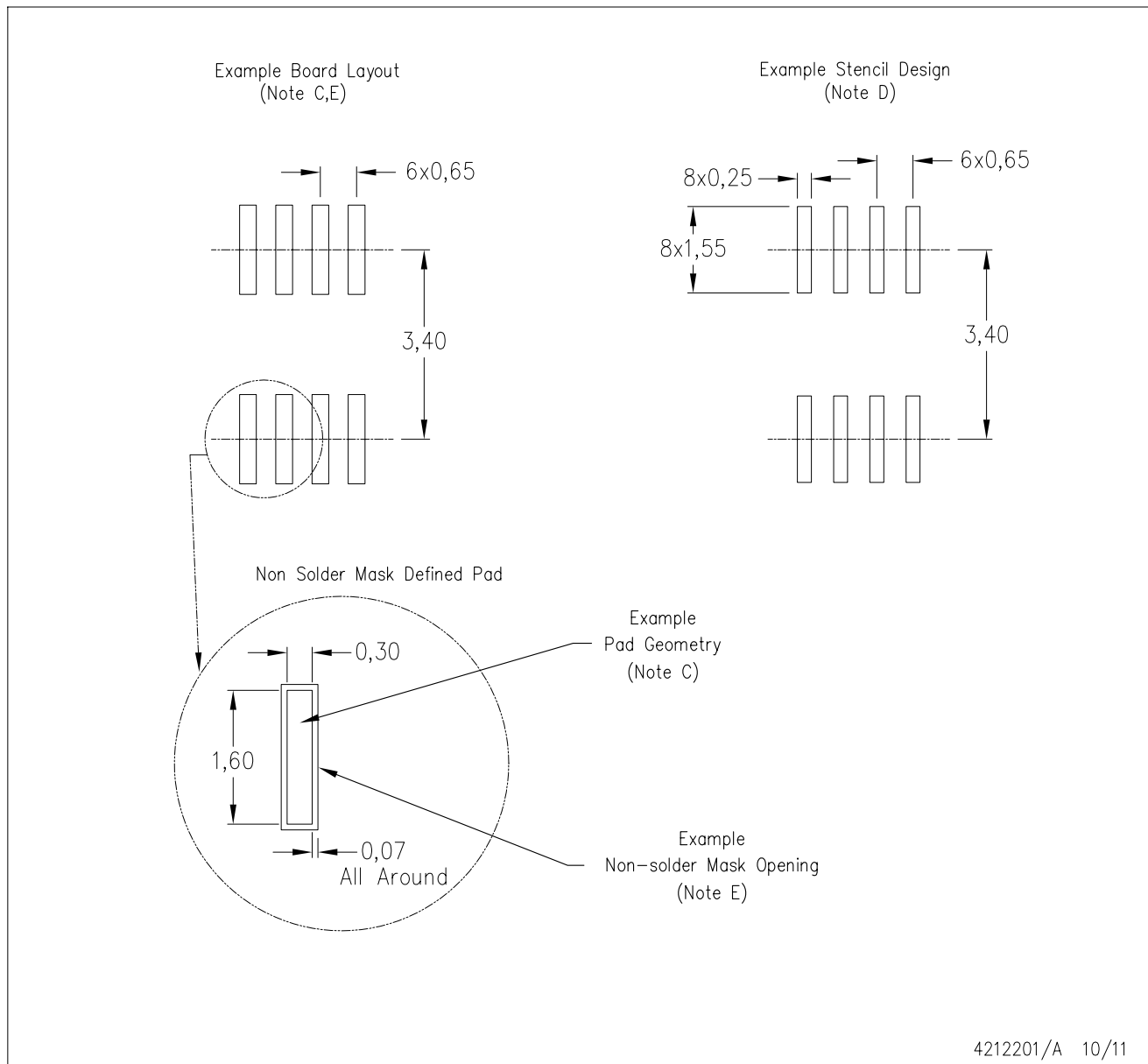
PLASTIC SMALL-OUTLINE PACKAGE



- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Body dimensions do not include mold flash or protrusion.
 - Falls within JEDEC MO-187 variation DA.

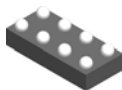
DCT (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525.
 - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

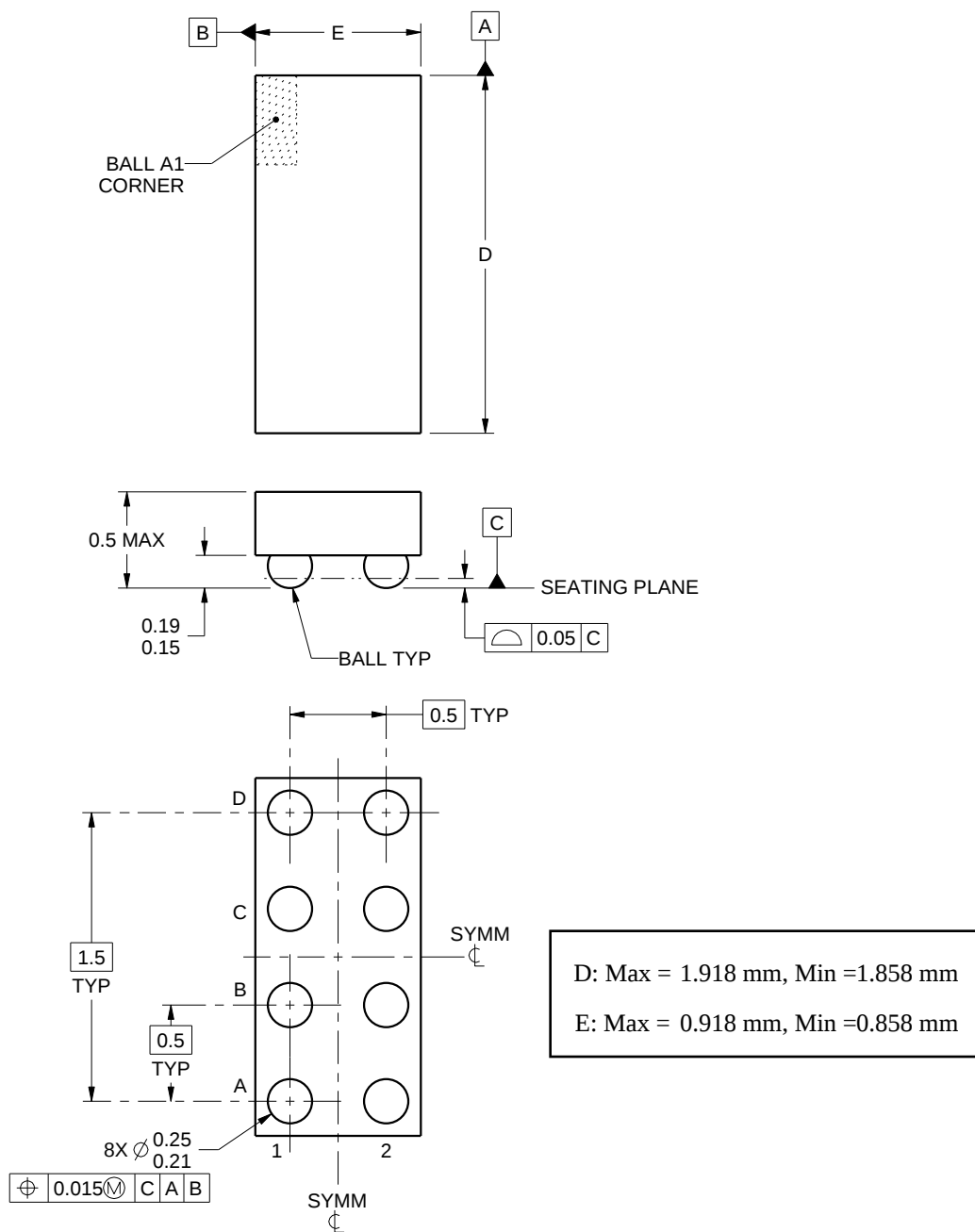
YZP0008



PACKAGE OUTLINE

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



4223082/A 07/2016

NOTES:

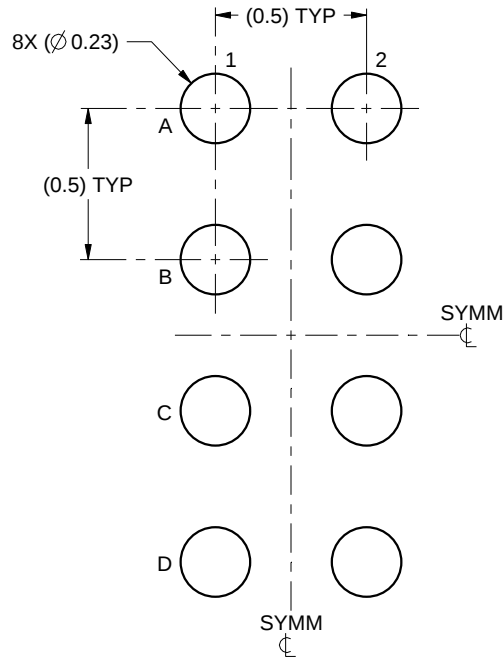
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

EXAMPLE BOARD LAYOUT

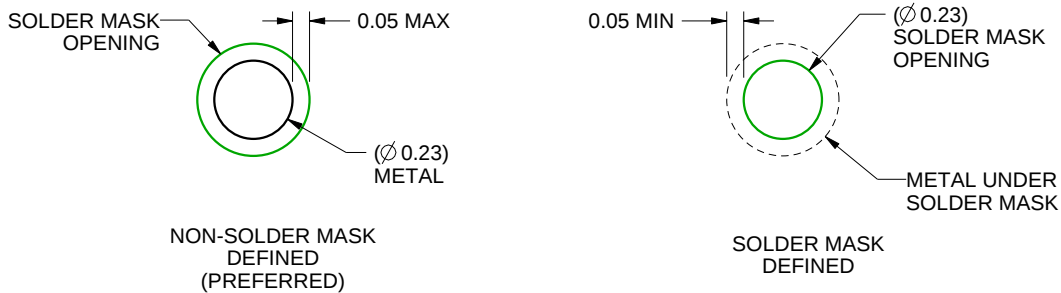
YZP0008

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



LAND PATTERN EXAMPLE
SCALE:40X



SOLDER MASK DETAILS
NOT TO SCALE

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NOTES: (continued)

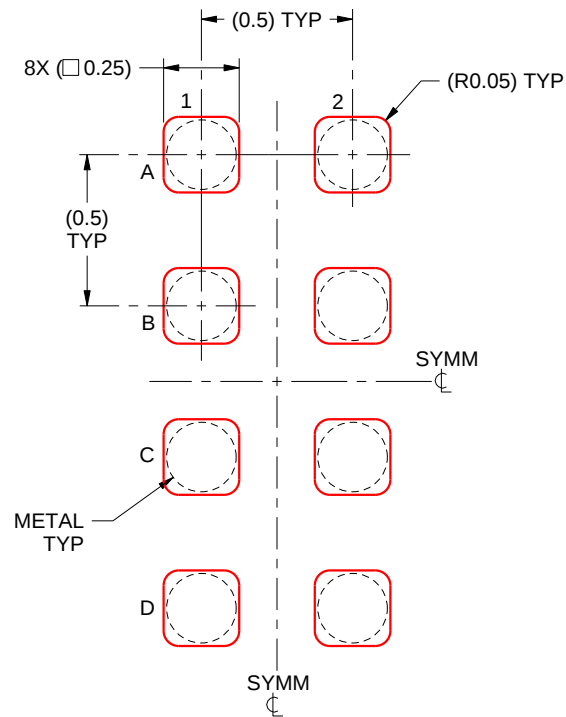
- Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).

EXAMPLE STENCIL DESIGN

YZP0008

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:40X

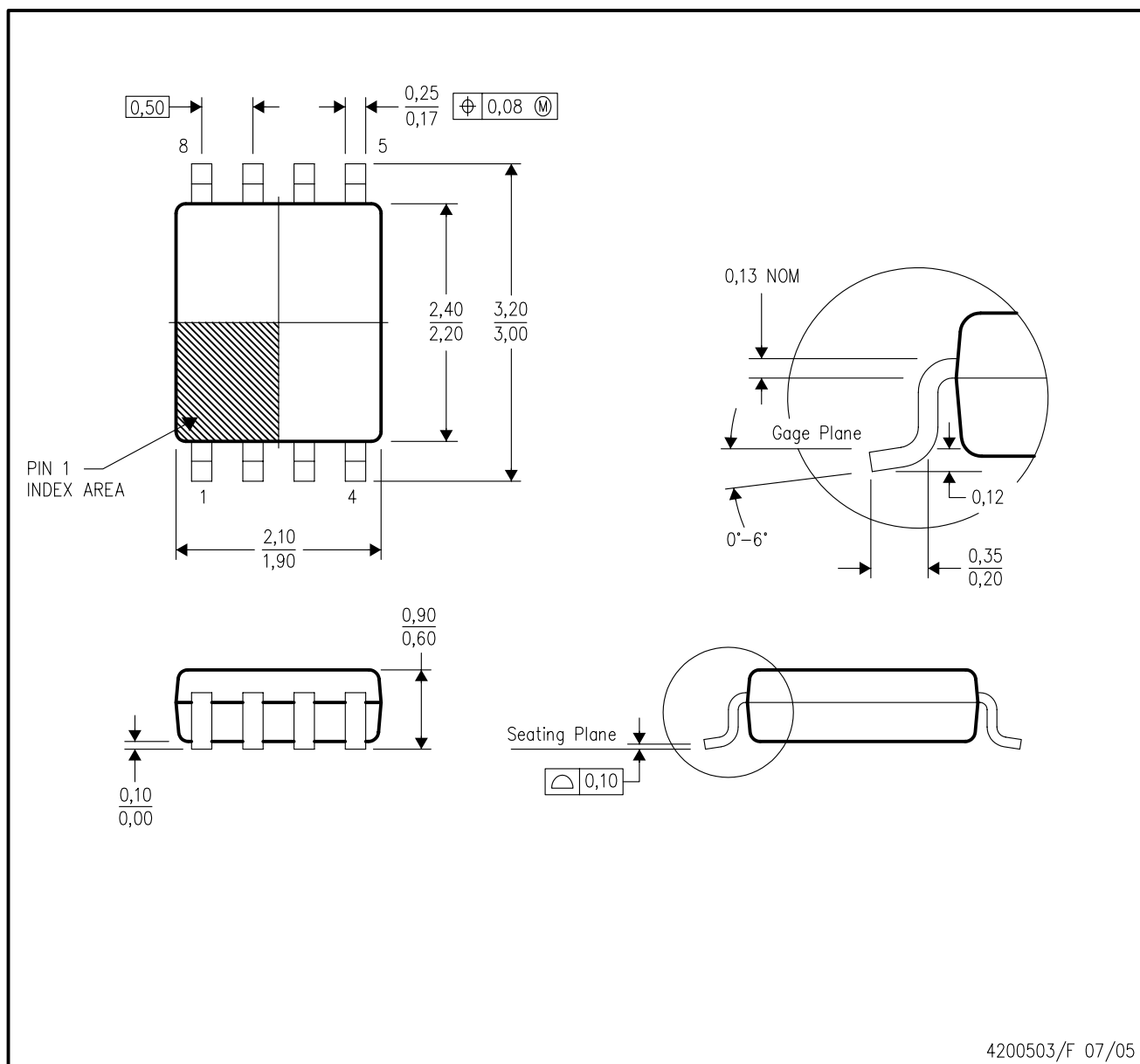
4223082/A 07/2016

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

DCU (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)

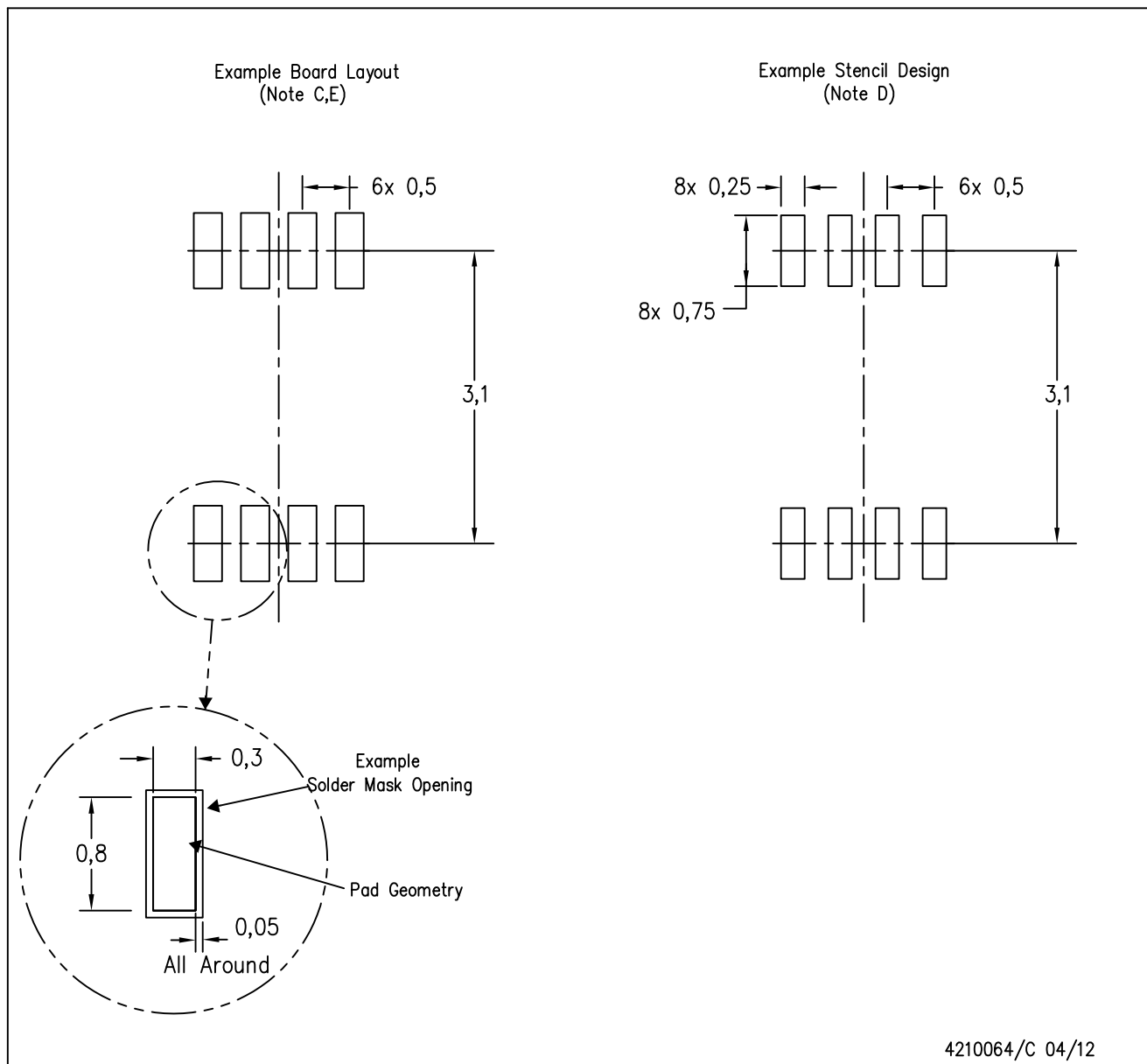


NOTES:

- All linear dimensions are in millimeters.
- This drawing is subject to change without notice.
- Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- Falls within JEDEC MO-187 variation CA.

DCU (S-PDSO-G8)

PLASTIC SMALL OUTLINE PACKAGE (DIE DOWN)



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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